



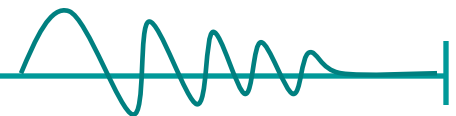
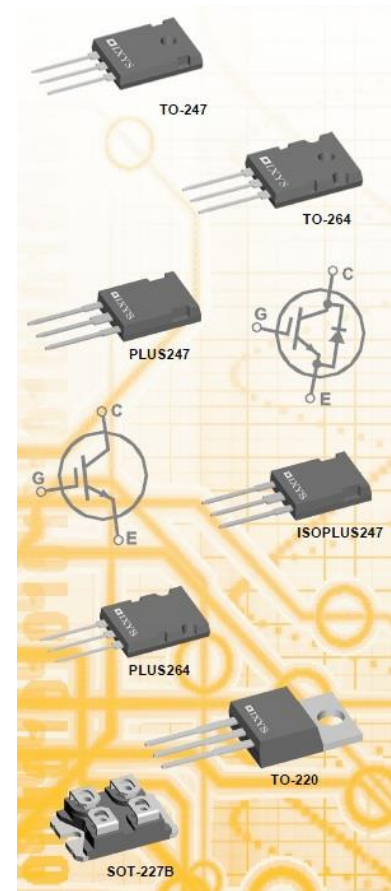
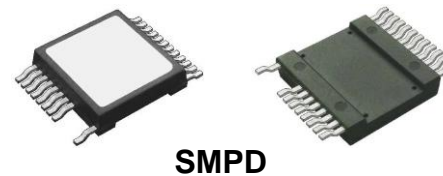
# 1200V XPT™ IGBTs

(for high-speed hard-switching applications)

IXYS Corporation  
October 2012

# Product Line Introduction (1200V XPT™ IGBTs)

- Broadest discrete IGBTs portfolio at 1200V (29 devices so far)
- From 7A to 120A current ratings at high temperature  $T_C = 110^\circ\text{C}$
- Manufactured through IXYS's state-of-the-art GenX3™ IGBT process and extreme-light Punch-Through (XPT™) design platform
- Designed for high-speed hard-switching power conversion applications
- Low turn-on and turn-off energy losses
- Low gate drive requirements
- Available in international standard packages
- Also available (upon request) in surface-mountable ultra-low profile SMPD and Mini-SMPD packages

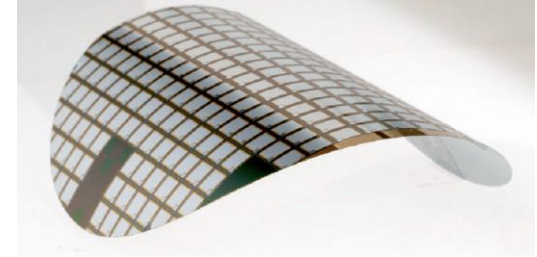


# Technology Advantages

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## Extreme-Light Punch-Through (XPT™) Design Platform

- Thin wafer technology
- Reduced thermal resistance ( $R_{thJC}$ )
- Higher current densities
- Reduced chip sizes
- Positive temperature coefficient of  $V_{CE(sat)}$



## Ultra-Fast Anti-Parallel Recovery Diodes

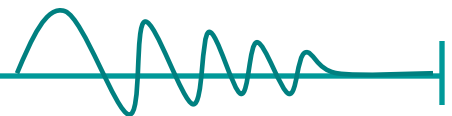
- Available with co-packed Sonic-FRED™ or HiPerFRED™ diodes
- Reduced turn-off losses and smooth switching waveforms
- Low electromagnetic interference (EMI)
- Short reverse recovery times ( $t_{rr}$ )

## Square Reverse Bias Safe Operating Areas (RBSOA)

- Up to the breakdown voltage of 1200V
- Ruggedness in snubberless hard-switching applications

# Summary Table (1200V XPT™ IGBTs)

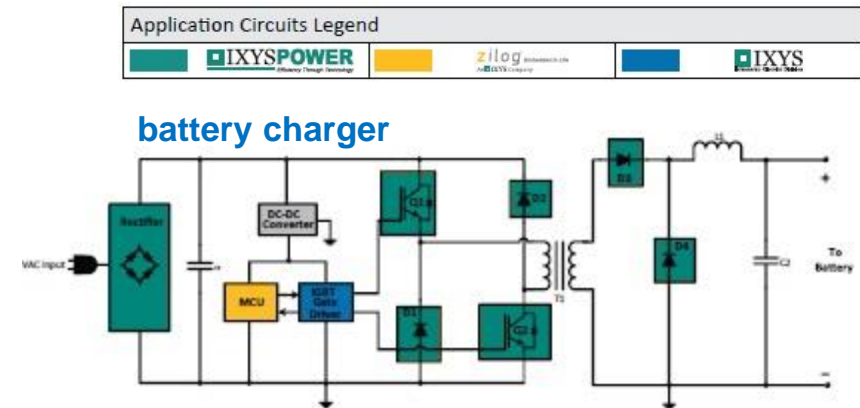
Part Number	$V_{CES}$ (V)	$I_{C25}$ $T_c=25^\circ\text{C}$ (A)	$I_{C110}$ $T_c=110^\circ\text{C}$ (A)	$V_{CE(sat)}$ max $T_j=25^\circ\text{C}$ (V)	$t_n$ typ $T_j=125^\circ\text{C}$ (ns)	$E_{off}$ typ $T_j=125^\circ\text{C}$ (mJ)	$R_{thJC}$ max IGBT ( $^\circ\text{C}/\text{W}$ )	Configuration	Package Style
IXYJ20N120C3D1	1200	16	7	4	105( $T_j=150^\circ\text{C}$ )	0.7( $T_j=150^\circ\text{C}$ )	1.78	Copacked (FRED)	ISO TO-247
IXYH20N120C3D1	1200	36	17	4	105( $T_j=150^\circ\text{C}$ )	0.7( $T_j=150^\circ\text{C}$ )	0.54	Copacked (FRED)	TO-247
IXYH20N120C3	1200	40	20	4	105( $T_j=150^\circ\text{C}$ )	0.7( $T_j=150^\circ\text{C}$ )	0.54	Single	TO-247
IXYP20N120C3	1200	40	20	4	105( $T_j=150^\circ\text{C}$ )	0.7( $T_j=150^\circ\text{C}$ )	0.54	Single	TO-220
IXYH30N120C3	1200	66	30	4	88	0.9	0.3	Single	TO-247
IXYH30N120C3D1	1200	66	30	4	88	0.9	0.3	Copacked (FRED)	TO-247
IXYP30N120C3	1200	66	30	4	88	0.9	0.3	Single	TO-220
IXYR50N120C3D1	1200	56	32 ( $T_c=90^\circ\text{C}$ )	4	60( $T_j=150^\circ\text{C}$ )	1.4 ( $T_j=150^\circ\text{C}$ )	0.43	Copacked (FRED)	ISOPLUS247
IXYH40N120B3	1200	96	40	2.9	206	2.05	0.26	Single	TO-247
IXYH40N120B3D1	1200	86	40	2.9	206	2.05	0.26	Copacked (FRED)	TO-247
IXYH40N120C3	1200	70	40	4	38	0.7	0.26	Single	TO-247
IXYH40N120C3D1	1200	64	40	4	38	0.7	0.26	Copacked (FRED)	TO-247
IXYN82N120C3	1200	105	46	3.2	95	3.7	0.25	Single	SOT-227B
IXYN82N120C3H1	1200	105	46	3.2	95	3.7	0.25	Copacked (FRED)	SOT-227B
IXYH50N120C3	1200	100	50	3.5	60( $T_j=150^\circ\text{C}$ )	1.4	0.2	Single	TO-247
IXYH50N120C3D1	1200	90	50	4	60( $T_j=150^\circ\text{C}$ )	1.4 ( $T_j=150^\circ\text{C}$ )	0.2	Copacked (FRED)	TO-247
IXYR100N120C3	1200	104	58	3.5	125	3.55	0.32	Single	ISOPLUS247
IXYN100N120C3H1	1200	134	62	3.5	125	3.55	0.18	Copacked (FRED)	SOT-227B
IXYB82N120C3H1	1200	160	82	3.2	95	3.7	0.12	Copacked (FRED)	PLUS264
IXYH82N120C3	1200	160	82	3.2	95	3.7	0.12	Single	TO-247
IXYN100N120C3	1200	152	86	3.5	125	3.55	0.18	Single	SOT-227B
IXYK100N120C3	1200	188	100	3.5	125	3.55	0.13	Single	TO-264
IXYX100N120C3	1200	188	100	3.5	125	3.55	0.13	Single	PLUS247
IXYK120N120C3	1200	220	120	3.5	120( $T_j=150^\circ\text{C}$ )	5.3 ( $T_j=150^\circ\text{C}$ )	0.1	Single	TO-264
IXYX120N120C3	1200	220	120	3.5	120( $T_j=150^\circ\text{C}$ )	5.3 ( $T_j=150^\circ\text{C}$ )	0.1	Single	PLUS247



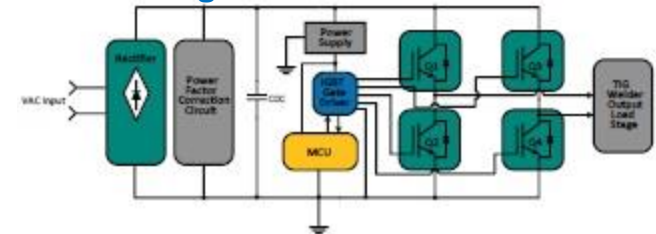
# Applications

Well-suited for high-speed hard-switching applications  
(up to 50kHz)

- Power inverters
- Uninterruptible Power Supplies (UPS)
- Switch-mode power supplies
- Power Factor Correction (PFC) circuits
- Battery chargers
- Welding machines
- Lamp ballasts



**TIG welding inverter**



# Punch Through (PT) vs. Extreme-Light Punch Through (XPT™)

## XPT™ IGBTs have:

- lower turn-on and turn-off energy losses
- lower gate drive requirements
- lower thermal resistance ( $R_{thJC}$ )
- higher power density

	IXGH40N120C3 (IXYS)	IXYH40N120C3 (IXYS)
Technology	<b>GenX3™ PT</b>	<b>GenX3™ XPT™</b>
$V_{CES}$	1200V	1200V
$I_C$ @ $T_c=110$ °C	40A	40A
$V_{CE(sat)}$ @ $T_j=25$ °C	4.4V	4V
Anti-parallel diode	No	No
$Q_{g(on)}$	142nC	85nC
$C_{ies}$	2930pF	1880pF
$C_{oes}$	225pF	115pF
$E_{off}$ @ $T_j=125$ °C	1.6mJ	0.7mJ
$R_{thJC(max)}$	0.33 °C/W	0.26 °C/W
$P_C$	380W	577W
Package type	TO-247	TO-247

